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ABSTRACT

A semiconductor device includes a transistor device, including a source and drain region, and a gate region. A bottom dielectric isolation layer is on a backside of the transistor device. A buffer layer is on a backside of the bottom dielectric isolation layer. A first conductive contact is positioned on a backside of the transistor device in contact with a backside of the source and drain region, through the bottom dielectric isolation layer and through the buffer layer. A second conductive contact is in contact with the gate region from a frontside of the gate region.

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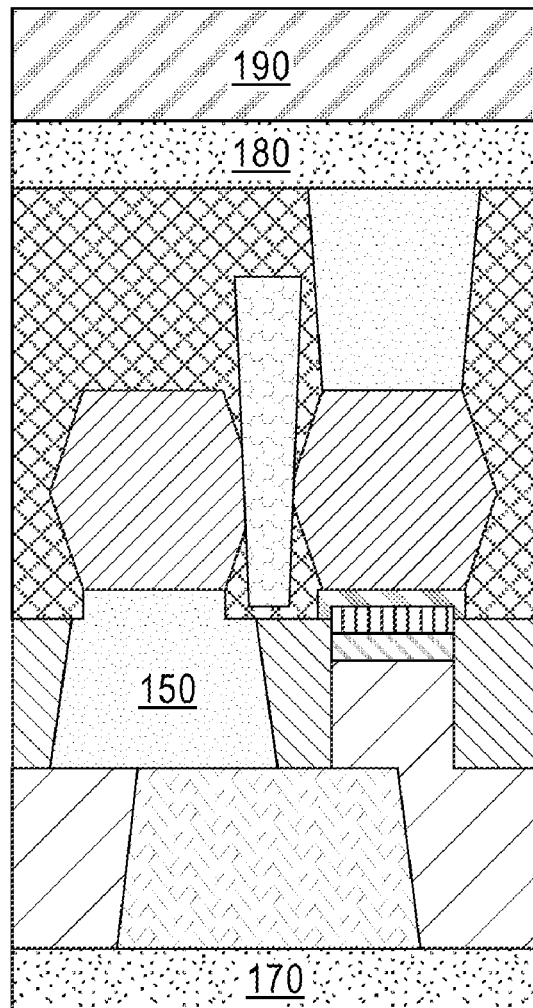
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